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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known	
				Application Number	10/801,219
				Filing Date	3/16/2004
				First Named Inventor	David J. Megaw
				Art Unit	N/A
				Examiner Name	National Semiconductor
				Attorney Docket Number	08211/0200387-US0/P05824
Sheet	1	of	1		

3 U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
JA	AA	US-6,342,781	01/29/02	Laraia	
JA	AB	US-4,808,908	02/28/1989	Lewis et al.	
JA	AC	US-4,443,753	04/17/1984	McGlinchey	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ²
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	MM-DD-YYYY			

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6 NON PATENT LITERATURE DOCUMENTS						
Examiner Initials [*]	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				T ²
JA	CA	AUDY, JONATHAN M. 3 rd order curvature corrected Bandgap Cell. IEEE, 1996, 397-400. (no month)				
JA	CB	AZARKAN, AHMIDOU, ARIE VAN STAVEREN and FABIANO FRUETT. A Low-noise Bandgap Reference Voltage Source with Curvature Correction. IEEE, 2002, 205-208. (no month)				
JA	CC	GUNAWAN, MADE ET AL. A Curvature-Corrected Low-Voltage Bandgap Reference. IEEE, 1993, 667670. (no month)				
JA	CD	GUPTA, SANDHYA and WILLIAM BLACK. A 3 to 5V CMOS Bandgap Voltage Reference with Novel Trimming. IEEE, 1997, 969-972. (no month)				
JA	CE	LEUNG, KA NANG, PHILIP K.T. MOK and CHI YAT LEUNG. A 2-V 23-μA 5.3-ppm/°C 4 th Order Curvature-Compensated CMOS Bandgap Reference. IEEE Custom Integrated Circuits Conference, 2002, 457-460. (no month)				
JA	CF	MICHEJDA, JOHN and SUK K. KIM. A Precision CMOS Bandgap Reference. IEEE Journal of Solid-State Circuits, December 1984, Vol. Sc 19:6: 1014-1021..				

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(S:1821 1102003)	J. Han	Date Considered	1/6/06
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